

ABSOLUTE MAXIMUM RATINGS ($T_j=25\text{ }^\circ\text{C}$, unless otherwise specified)**Inverter part IGBT/FWDI**

Symbol	Item	Conditions	Rating	Unit
V_{CES}	Collector-emitter voltage	G-E short-circuited	1200	V
V_{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I_C	Collector current	DC, $T_C=119\text{ }^\circ\text{C}$ (Note.2)	100	A
I_{CRM}		Pulse (Note.3)	200	
P_{tot}	Total power dissipation	$T_C=25\text{ }^\circ\text{C}$ (Note.2, 4)	750	W
I_E (Note.1)	Emitter current	$T_C=25\text{ }^\circ\text{C}$ (Note.2, 4)	100	A
I_{ERM} (Note.1)		Pulse (Note.3)	200	

Module

Symbol	Item	Conditions	Rating	Unit
T_{jmax}	Maximum junction temperature	-	175	$^\circ\text{C}$
T_{Cmax}	Maximum case temperature	(Note.2)	125	
T_{jop}	Operating junction temperature	-	-40 ~ +150	$^\circ\text{C}$
T_{stg}	Storage temperature	-	-40 ~ +125	
V_{isol}	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	2500	V

ELECTRICAL CHARACTERISTICS ($T_j=25\text{ }^\circ\text{C}$, unless otherwise specified)**Inverter part IGBT/FWDI**

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I_{CES}	Collector-emitter cut-off current	$V_{CE}=V_{CES}$, G-E short-circuited	-	-	1	mA	
I_{GES}	Gate-emitter leakage current	$V_{GE}=V_{GES}$, C-E short-circuited	-	-	0.5	μA	
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C=10\text{ mA}$, $V_{CE}=10\text{ V}$	5.4	6.0	6.6	V	
V_{CESat} (Terminal)	Collector-emitter saturation voltage	$I_C=100\text{ A}$ (Note.5), $V_{GE}=15\text{ V}$	$T_j=25\text{ }^\circ\text{C}$	-	1.80	2.25	V
			$T_j=125\text{ }^\circ\text{C}$	-	2.00	-	
			$T_j=150\text{ }^\circ\text{C}$	-	2.05	-	
V_{CESat} (Chip)	Collector-emitter saturation voltage	$I_C=100\text{ A}$ (Note.5), $V_{GE}=15\text{ V}$	$T_j=25\text{ }^\circ\text{C}$	-	1.70	2.15	V
			$T_j=125\text{ }^\circ\text{C}$	-	1.90	-	
			$T_j=150\text{ }^\circ\text{C}$	-	1.95	-	
C_{ies}	Input capacitance	$V_{CE}=10\text{ V}$, G-E short-circuited	-	-	10	nF	
C_{oes}	Output capacitance		-	-	2.0		
C_{res}	Reverse transfer capacitance		-	-	0.17		
Q_G	Gate charge	$V_{CC}=600\text{ V}$, $I_C=100\text{ A}$, $V_{GE}=15\text{ V}$	-	233	-	nC	
$t_{d(on)}$	Turn-on delay time	$V_{CC}=600\text{ V}$, $I_C=100\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=6.2\text{ }\Omega$, Inductive load	-	-	300	ns	
t_r	Rise time		-	-	200		
$t_{d(off)}$	Turn-off delay time		-	-	600		
t_f	Fall time		-	-	300		
V_{EC} (Note.1) (Terminal)	Emitter-collector voltage	$I_E=100\text{ A}$ (Note.5), G-E short-circuited	$T_j=25\text{ }^\circ\text{C}$	-	1.8	2.25	V
			$T_j=125\text{ }^\circ\text{C}$	-	1.8	-	
			$T_j=150\text{ }^\circ\text{C}$	-	1.8	-	
V_{EC} (Note.1) (Chip)	Emitter-collector voltage	$I_E=100\text{ A}$ (Note.5), G-E short-circuited	$T_j=25\text{ }^\circ\text{C}$	-	1.7	2.15	V
			$T_j=125\text{ }^\circ\text{C}$	-	1.7	-	
			$T_j=150\text{ }^\circ\text{C}$	-	1.7	-	
t_{rr} (Note.1)	Reverse recovery time	$V_{CC}=600\text{ V}$, $I_E=100\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=6.2\text{ }\Omega$, Inductive load	-	-	300	ns	
Q_{rr} (Note.1)	Reverse recovery charge		-	5.3	-	μC	
E_{on}	Turn-on switching energy per pulse	$V_{CC}=600\text{ V}$, $I_C=I_E=100\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=6.2\text{ }\Omega$, $T_j=150\text{ }^\circ\text{C}$, Inductive load	-	8.6	-	mJ	
E_{off}	Turn-off switching energy per pulse		-	10.7	-		
E_{rr} (Note.1)	Reverse recovery energy per pulse		-	10.2	-		
$R_{CC'+EE'}$	Internal lead resistance	Main terminals-chip, per switch, $T_C=25\text{ }^\circ\text{C}$ (Note.2)	-	-	2.2	m Ω	
r_g	Internal gate resistance	Per switch	-	0	-	Ω	

ELECTRICAL CHARACTERISTICS (cont.; T_j=25 °C, unless otherwise specified)

NTC thermistor part

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R ₂₅	Zero power resistance	T _C =25 °C (Note.2)	4.85	5.00	5.15	kΩ
ΔR/R	Deviation of resistance	T _C =100 °C, R ₁₀₀ =493 Ω	-7.3	-	+7.8	%
B _(25/50)	B constant	Approximate by equation (Note.6)	-	3375	-	K
P ₂₅	Power dissipation	T _C =25 °C (Note.2)	-	-	10	mW

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R _{th(j-c)Q}	Thermal resistance (Note. 2)	Junction to case, per IGBT	-	-	0.20	K/W
R _{th(j-c)D}		Junction to case, per FWDi	-	-	0.29	
R _{th(c-s)}	Contact thermal resistance (Note. 2)	Case to heat sink, per 1 module, Thermal grease applied (Note.7)	-	15	-	K/kW

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M _s	Mounting torque	Mounting to heat sink M 5 screw	2.5	3.0	3.5	N·m
d _s	Creepage distance	Terminal to terminal	10.28	-	-	mm
		Terminal to base plate	14.27	-	-	
d _a	Clearance	Terminal to terminal	10.28	-	-	mm
		Terminal to base plate	12.33	-	-	
m	Weight	-	-	300	-	g
e _c	Flatness of base plate	On the centerline X, Y (Note.8)	±0	-	+100	μm

Note.1: Represent ratings and characteristics of the anti-parallel, emitter-collector free wheeling diode (FWDi).

Note.2: Case temperature (T_c) and heat sink temperature (T_s) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.
The heat sink thermal resistance should measure just under the chips.

Note.3: Pulse width and repetition rate should be such that the device junction temperature (T_j) dose not exceed T_{jmax} rating.

Note.4: Junction temperature (T_j) should not increase beyond T_{jmax} rating.

Note.5: Pulse width and repetition rate should be such as to cause negligible temperature rise.

Refer to the figure of test circuit for V_{CEsat}, V_{EC}.

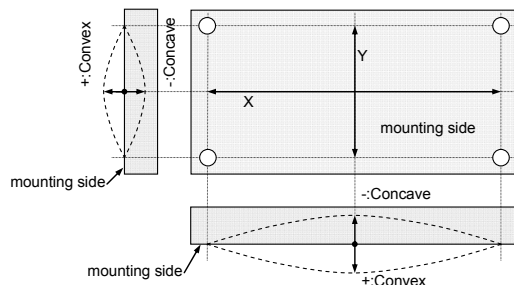
Note.6: $B_{(25/50)} = \ln\left(\frac{R_{25}}{R_{50}}\right) / \left(\frac{1}{T_{25}} - \frac{1}{T_{50}}\right)$,

R₂₅: resistance at absolute temperature T₂₅ [K]; T₂₅=25 [°C]+273.15=298.15 [K]

R₅₀: resistance at absolute temperature T₅₀ [K]; T₅₀=50 [°C]+273.15=323.15 [K]

Note.7: Typical value is measured by using thermally conductive grease of λ=0.9 W/(m·K).

Note.8: The base plate (mounting side) flatness measurement points (X, Y) are as follows of the following figure.



Note.9: Japan Electronics and Information Technology Industries Association (JEITA) standards,

"EIAJ ED-4701/300: Environmental and endurance test methods for semiconductor devices (Stress test I)"

Note.10: Use the following screws when mounting the printed circuit board (PCB) on the stand offs.

"M2.6×10 or M2.6×12 self tapping screw"

The length of the screw depends on the thickness of the PCB.

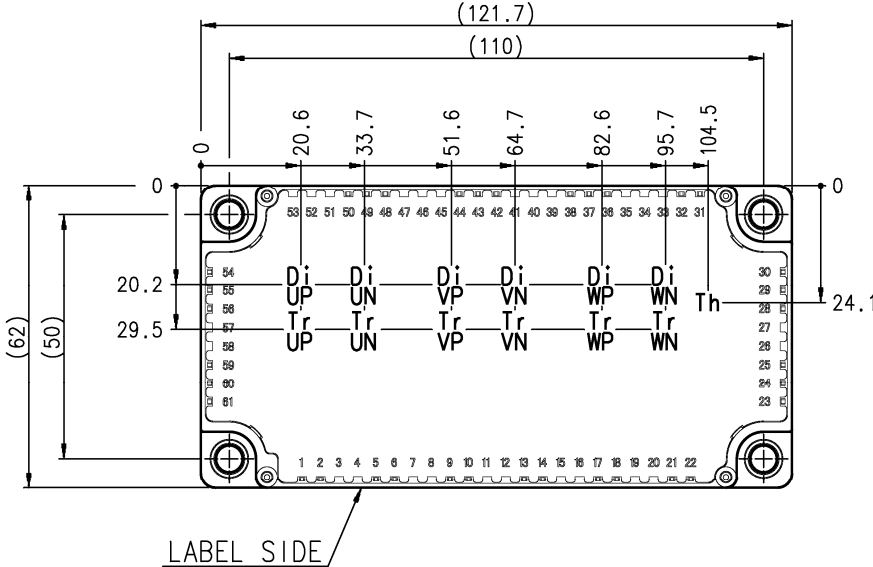
MITSUBISHI IGBT MODULES
CM100TX-24S
 HIGH POWER SWITCHING USE
 INSULATED TYPE

RECOMMENDED OPERATING CONDITIONS ($T_a=25\text{ }^\circ\text{C}$, unless otherwise specified)

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
V_{CC}	DC supply voltage	Applied across P-N / P1-N1 terminals	-	600	850	V
V_{GEon}	Gate-emitter drive voltage	Applied across G*P-Es*P / G*N-Es*N terminals	13.5	15.0	16.5	V
R_G	External gate resistance	Per switch	6.2	-	62	Ω

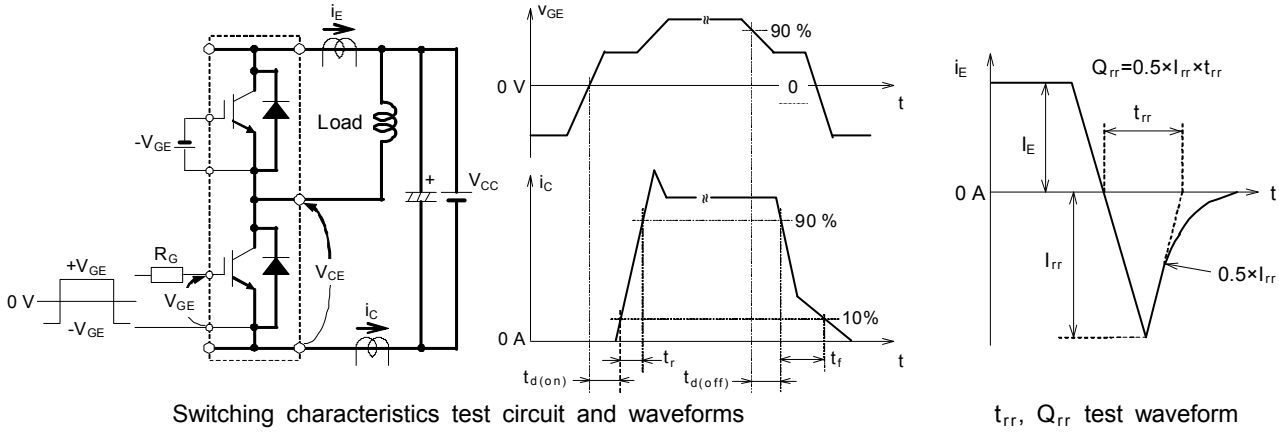
CHIP LOCATION (Top View)

Dimension in mm, Tolerance: $\pm 1\text{ mm}$



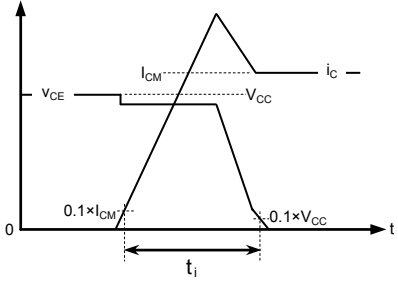
Tr*P/Tr*N: IGBT, Di*P/Di*N: FWDi, Th: NTC thermistor. Each mark points the center position of each chip.

TEST CIRCUIT AND WAVEFORMS

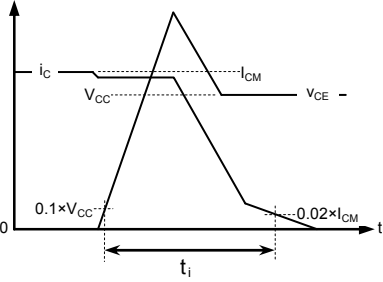


Switching characteristics test circuit and waveforms

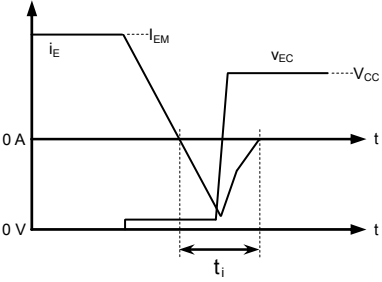
t_{rr} , Q_{rr} test waveform



IGBT Turn-on switching energy



IGBT Turn-off switching energy

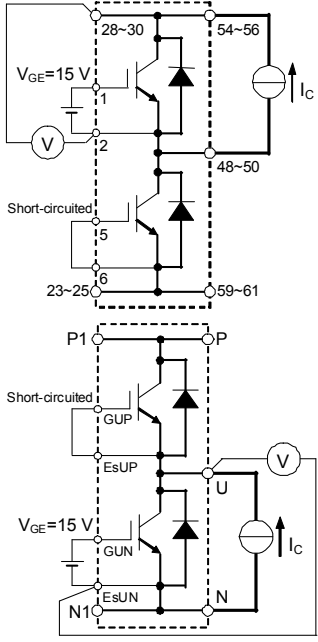


FWDi reverse recovery energy

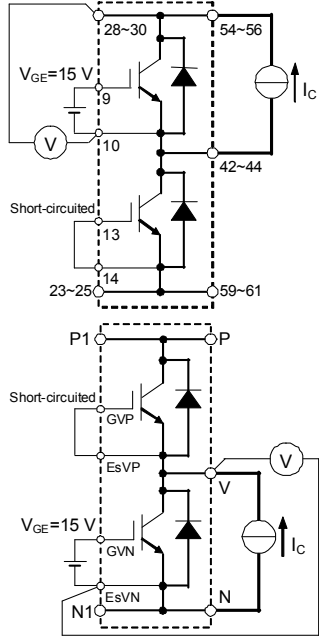
Turn-on / Turn-off switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

MITSUBISHI IGBT MODULES
CM100TX-24S
 HIGH POWER SWITCHING USE
 INSULATED TYPE

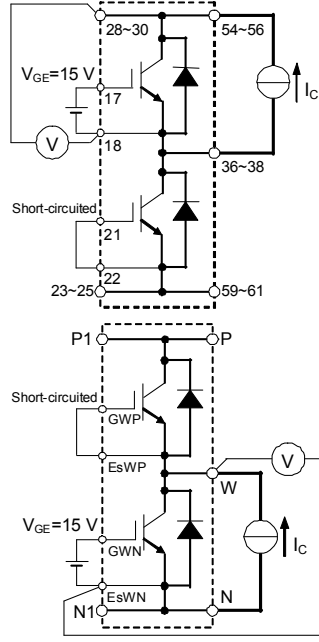
TEST CIRCUIT



Gate-emitter short-circuited
 GVP-EsVP, GWP-EsWP,
 GVN-EsVN, GWN-EsWN
UP / UN IGBT

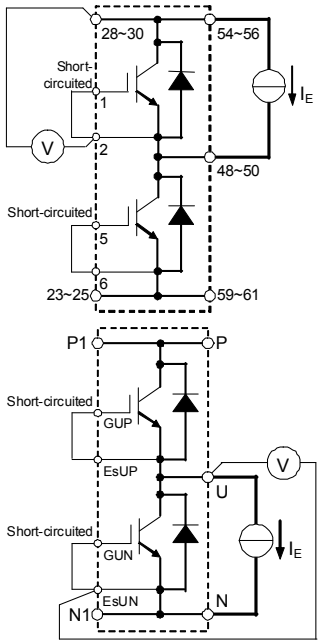


Gate-emitter short-circuited
 GUP-EsUP, GWP-EsWP,
 GUN-EsUN, GWN-EsWN
VP / VN IGBT

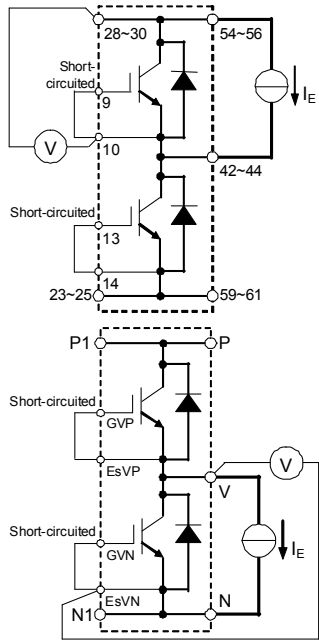


Gate-emitter short-circuited
 GUP-EsUP, GVP-EsVP,
 GUN-EsUN, GVN-EsVN
WP / WN IGBT

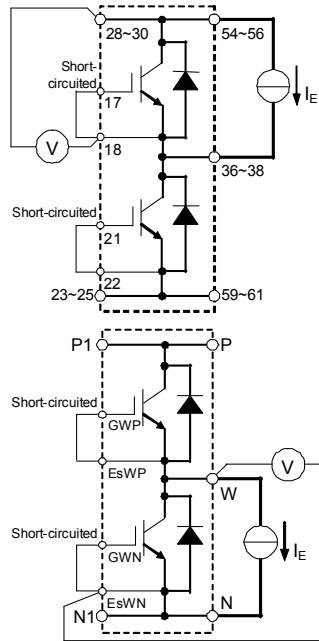
V_{CEsat} TEST CIRCUIT



Gate-emitter short-circuited
 GVP-EsVP, GWP-EsWP,
 GVN-EsVN, GWN-EsWN
UP / UN FWDi



Gate-emitter short-circuited
 GUP-EsUP, GWP-EsWP,
 GUN-EsUN, GWN-EsWN
VP / VN FWDi



Gate-emitter short-circuited
 GUP-EsUP, GVP-EsVP,
 GUN-EsUN, GVN-EsVN
WP / WN FWDi

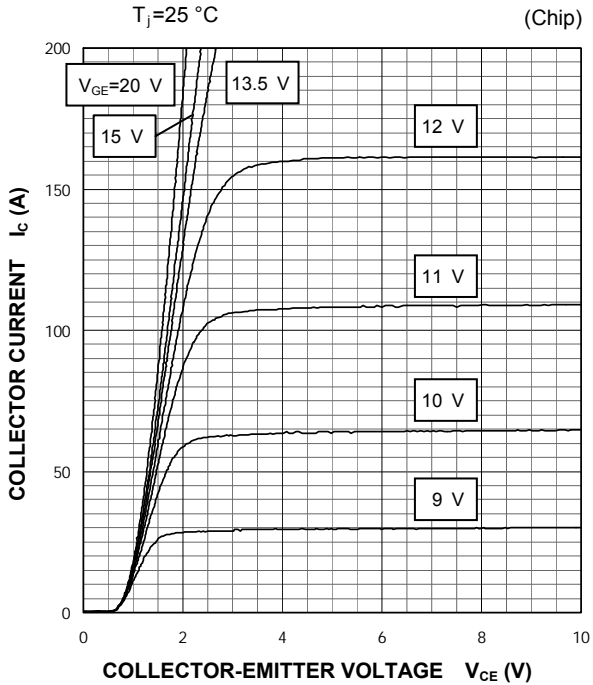
V_{EC} TEST CIRCUIT

* In the above test circuit, should use all three main pin terminals (P/N/U/V/W) for connection with the terminals and the current source.

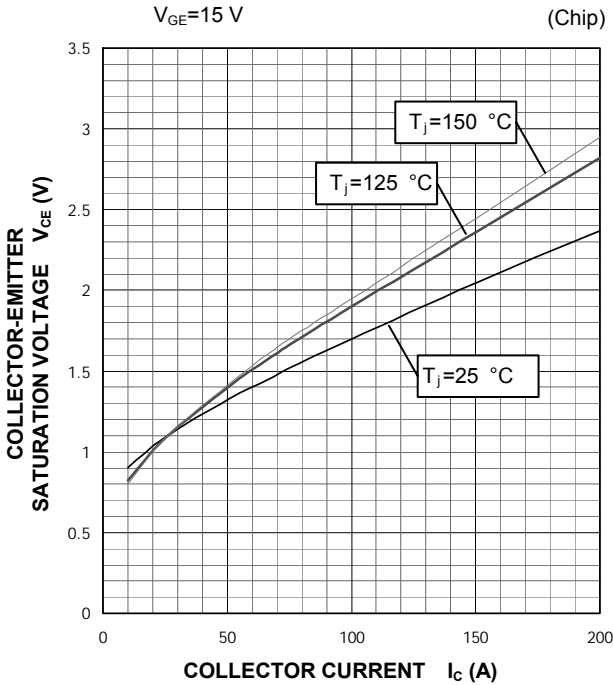
PERFORMANCE CURVES

INVERTER PART

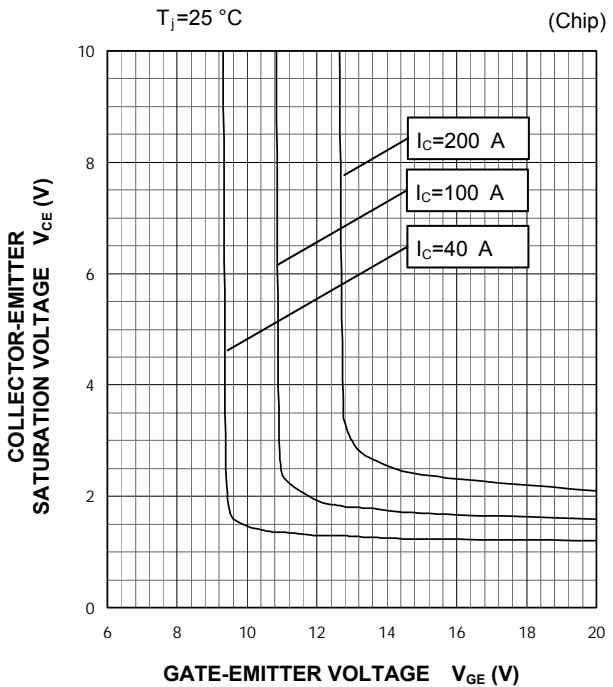
OUTPUT CHARACTERISTICS (TYPICAL)



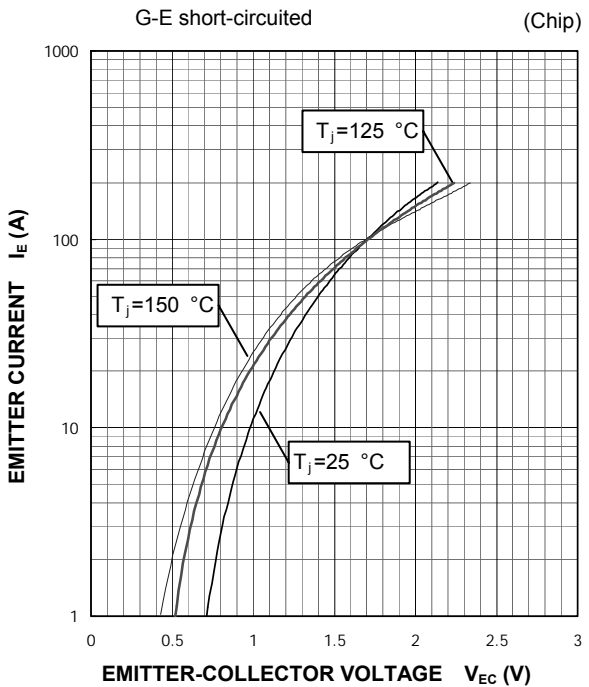
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



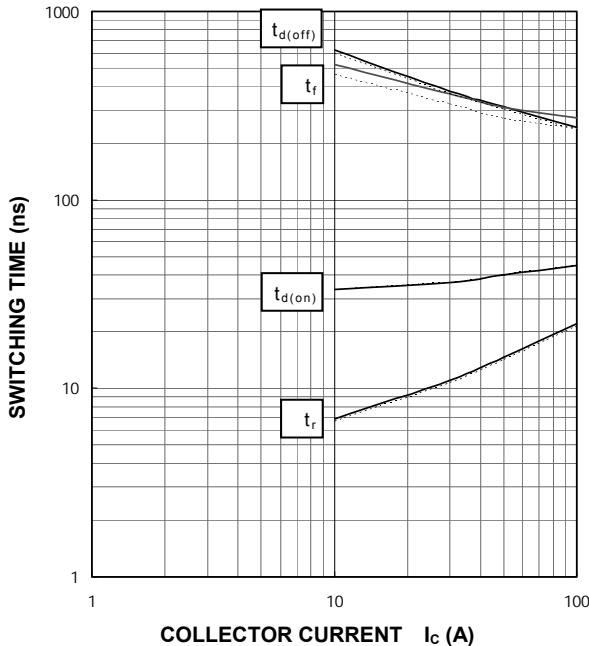
FREE WHEELING DIODE FORWARD CHARACTERISTICS (TYPICAL)



MITSUBISHI IGBT MODULES
CM100TX-24S
 HIGH POWER SWITCHING USE
 INSULATED TYPE

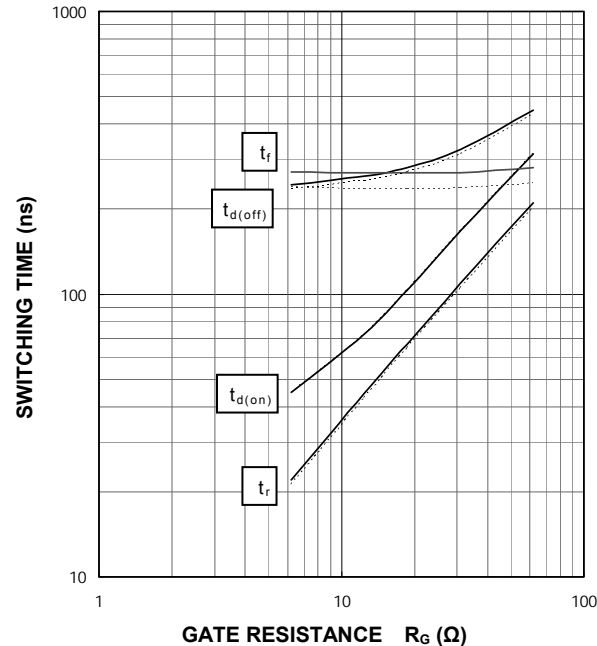
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=6.2\ \Omega$,
 —: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



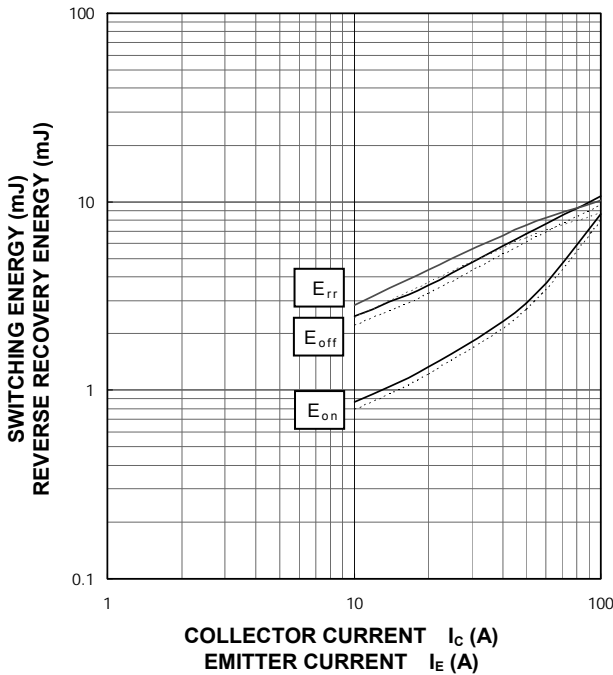
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $I_C=100\text{ A}$,
 —: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



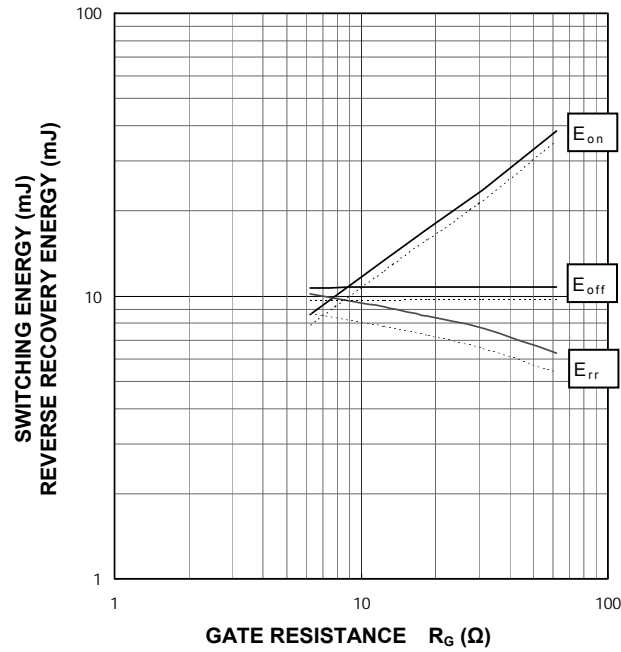
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=6.2\ \Omega$,
 —: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



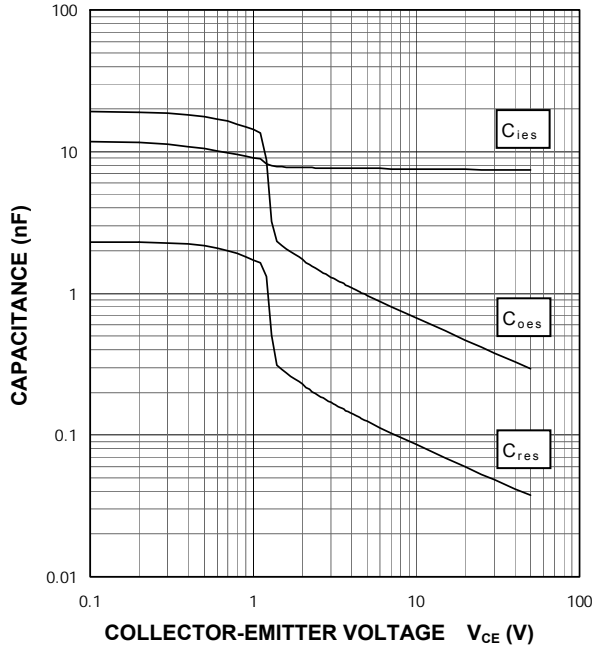
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $I_C=100\text{ A}$,
 —: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



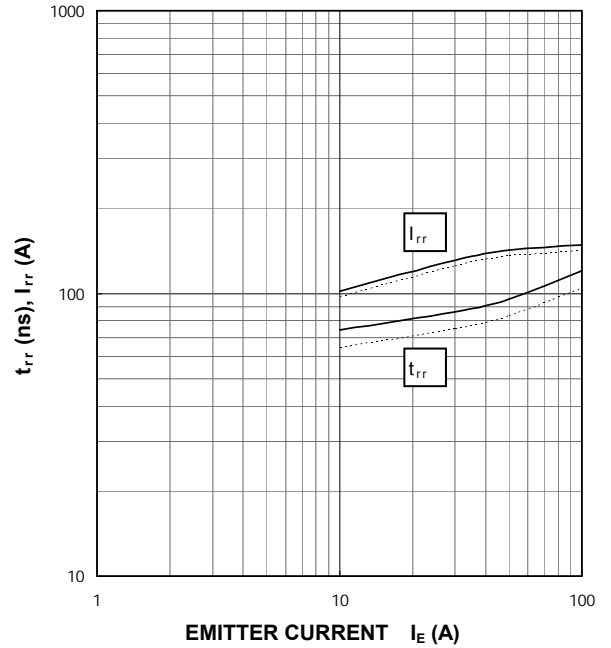
**CAPACITANCE CHARACTERISTICS
 (TYPICAL)**

G-E short-circuited, $T_j=25\text{ }^\circ\text{C}$



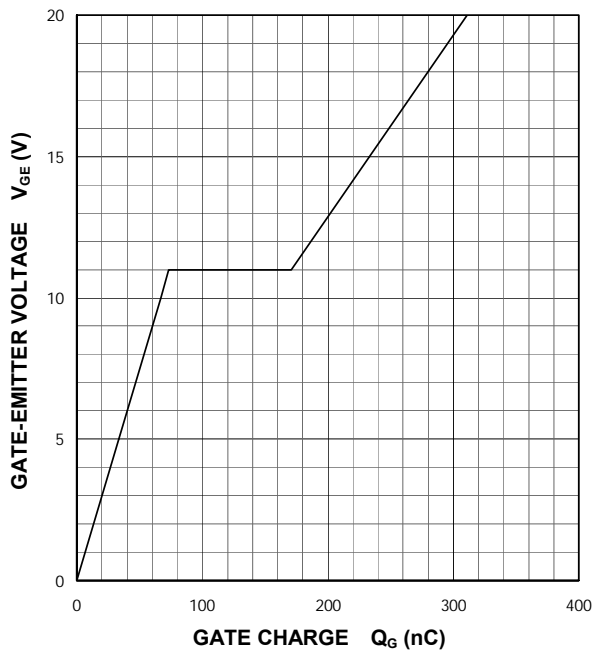
**FREE WHEELING DIODE
 REVERSE RECOVERY CHARACTERISTICS
 (TYPICAL)**

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=6.2\ \Omega$,
 —: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



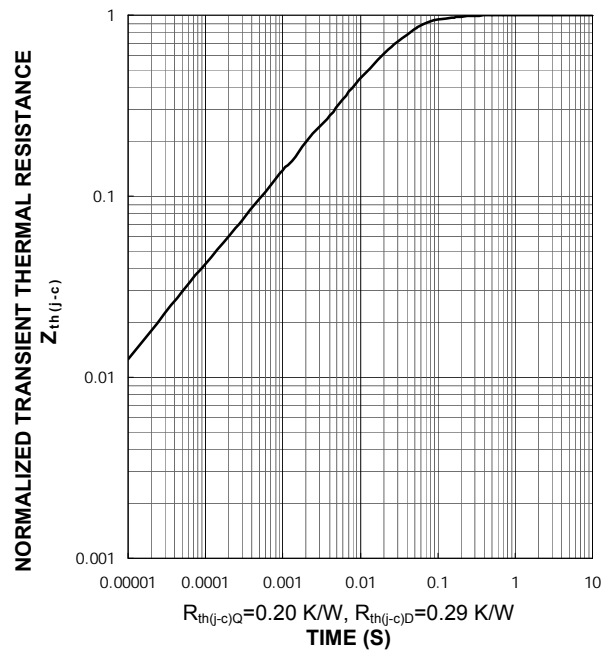
**GATE CHARGE CHARACTERISTICS
 (TYPICAL)**

$V_{CC}=600\text{ V}$, $I_C=100\text{ A}$, $T_j=25\text{ }^\circ\text{C}$



**TRANSIENT THERMAL IMPEDANCE
 CHARACTERISTICS
 (MAXIMUM)**

Single pulse, $T_C=25\text{ }^\circ\text{C}$



Keep safety first in your circuit designs!

· Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

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